

Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i>				Complete if Known	
				Application Number	10/581,950-Conf. #8737
				Filing Date	August 18, 2008
				First Named Inventor	Anderson
				Art Unit	2822
				Examiner Name	D. T. Nguyen
Sheet	1	of	1	Attorney Docket Number	GWS-008

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	A12*	US-5,945,730	08-31-1999	Sicard et al.	
	A13*	US-6,261,944	07-17-2001	Mehta et al.	
	A14*	US-6,507,070	01-14-2003	Shen et al.	
	A15*	US-6,586,323	07-01-2003	Fan et al.	
	A16*	US-6,674,157	01-06-2004	Lang	
	A17*	US-6,861,702	03-01-2005	Kitamura et al.	
	A18*	US-6,936,923	08-30-2005	Lin et al.	
	A19*	US-7,432,595	10-07-2008	Okada	

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)			
	B1	WO-2005-057617 A3	06-23-2005	Great Wall Semiconductor	

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
	C4	Darwish et al., "Scaling Issues in Lateral Power MOSFETs," Proc. 1998 Intl. Symp. On Power Semiconductor Devices & Ics, pp. 329-332.	
	C5	International Search Report and Written Opinion for PCT/US2004/040698, dated August 8, 2005.	
	C6	International Search Report and Written Opinion for PCT/US2004/40197, mailed November 21, 2008.	
	C7	Pavier et al., "Bi-directional FlipFET™ MOSFETS for Cell Phone Battery Protection Circuits," PCIM 2001.	
	C8	Shen et al., "Lateral Discrete Power MOSFET: Enabling Technology for Next-Generation, MHz-Frequency, High-Density DC/DC Converters," APEC (2004).	
	C9	Sun et al., "0.35μm, 43 μΩcm ² 6mΩ Power MOSFET to Power Future Microprocessor," IEEE pp. 77-79 (1999).	
Examiner Signature			Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. * CITE NO.: Those application(s) which are marked with an single asterisk (*) next to the Cite No. are not supplied (under 37 CFR 1.98(a)(2)(iii)) because that application was filed after June 30, 2003 or is available in the IFW. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

LIBC/3561130